TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

131,072-WORD BY 8-BIT CMOS STATIC RAM

DESCRIPTION

The TC558128BJ/BFT is a 1,048,576-bit high-speed static random access memory (SRAM) organized as 131,072 words by 8 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed, it operates from a single 5 V power supply. There are two control inputs. Chip enable ($\overline{CE}$) can be used to place the device in a low-power mode, and output enable ($\overline{OE}$) provides fast memory access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly TTL compatible. The TC558128BJ/BFT is available in a plastic 32-pin SOJ (400 mil width) and TSOP packages for high density surface assembly.

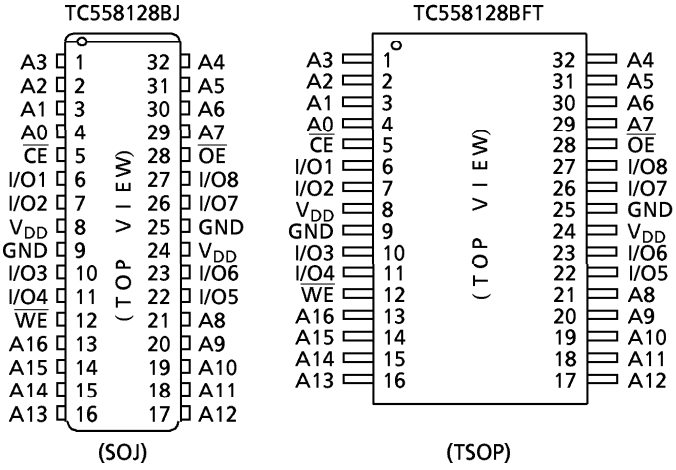
FEATURES

- Fast access time (the following are maximum values)
  TC558128BJ/BFT-12: 12 ns
  TC558128BJ/BFT-15: 15 ns
- Low-power dissipation
  (the following are maximum values)

Cycle Time	12	15	20	25	30	ns
Operation (max)	190	170	140	130	120	mA

  Standby: 1 mA (both devices)
- Single power supply voltage of 5 V ± 10%.
- Fully static operation
- All inputs and outputs are TTL compatible
- Output buffer control using $\overline{OE}$
- Package:
  SOJ32-P-400-1.27A (BJ) (Weight: 1.22 g typ)
  TSOP II 32-P-400-0.80C (BFT) (Weight: 0.34 g typ)

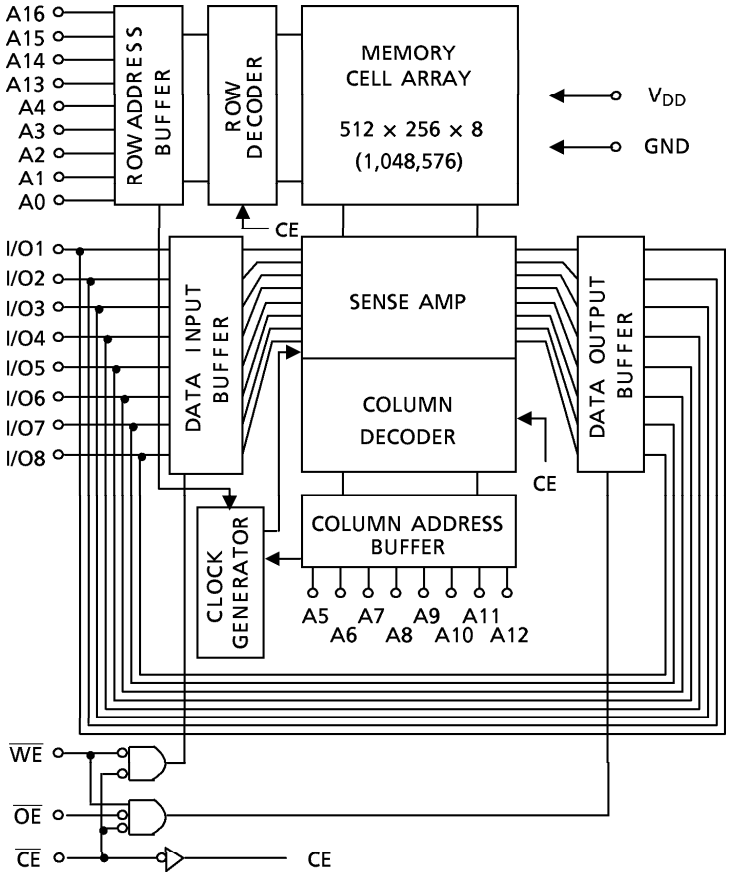
PIN ASSIGNMENT



PIN NAMES

A0 to A16	Address Inputs
I/O1 to I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable
V_{DD}	Power (+ 5 V)
GND	Ground

BLOCK DIAGRAM



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	− 0.5 to 7.0	V
V_{IN}	Input Terminal Voltage	− 2.0 * to 7.0	V
$V_{I/O}$	Input/Output Terminal Voltage	− 0.5 * to V_{DD} + 0.5	V
P_D	Power Dissipation	1.1	W
T_{solder}	Soldering Temperature (10 s)	260	°C
T_{strg}	Storage Temperature	− 65 to 150	°C
T_{opr}	Operating Temperature	− 10 to 85	°C

*: − 3 V with a pulse width of 10 ns

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V_{IH}	Input High Voltage	2.2	–	V_{DD} + 0.5	V
V_{IL}	Input Low Voltage	– 0.5 *	–	0.8	V

*: – 3 V with a pulse width of 10 ns

DC CHARACTERISTICS (Ta = 0° to 70°C, V_{DD} = 5 V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0 V to V_{DD}		–	–	± 10	μA
I_{LO}	Output Leakage Current	$\overline{CE}$ = V_{IH} or $\overline{WE}$ = V_{IL} or $\overline{OE}$ = V_{IH} V_{OUT} = 0 V to V_{DD}		–	–	± 10	μA
I_{OH}	Output High Current	V_{OH} = 2.4 V		– 4	–	–	mA
I_{OL}	Output Low Current	V_{OL} = 0.4 V		8	–	–	mA
I_{DDO}	Operating Current	$\overline{CE}$ = V_{IL}, Iout = 0 mA Other Inputs = V_{IH} or V_{IL}	tcycle = 12 ns	–	–	190	mA
			tcycle = 15 ns	–	–	170	
			tcycle = 20 ns	–	–	140	
			tcycle = 25 ns	–	–	130	
			tcycle = 30 ns	–	–	120	
I_{DDS1}	Standby Current	$\overline{CE}$ = V_{IH}, Other Inputs = V_{IH} or V_{IL}		–	–	30	mA
I_{DDS2}		$\overline{CE}$ = V_{DD} – 0.2 V Other Inputs = V_{DD} – 0.2 V or 0.2 V		–	–	1	

CAPACITANCE (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	V_{IN} = GND	6	pF
$C_{I/O}$	Input/Output Capacitance	$V_{I/O}$ = GND	8	pF

Note: This parameter is periodically sampled and is not 100% tested.

OPERATING MODE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O1 to I/O8	POWER
Read	L	L	H	Output	I_{DDO}
Write	L	×	L	Input	I_{DDO}
Outputs Disable	L	H	H	High Impedance	I_{DDO}
Standby	H	×	×	High Impedance	I_{DDS}

×: Don't care

AC CHARACTERISTICS (Ta = 0° to 70°C (Note 1), V_{DD} = 5 V ± 10%)

READ CYCLE

SYMBOL	PARAMETER	TC558128BJ/BFT-12		TC558128BJ/BFT-15		UNIT
		MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	12	–	15	–	ns
t_{ACC}	Address Access Time	–	12	–	15	
t_{CO}	Chip Enable Access Time	–	12	–	15	
t_{OE}	Output Enable Access Time	–	6	–	8	
t_{OH}	Output Data Hold Time from Address Change	5	–	5	–	
t_{COE}	Output Enable Time from Chip Enable	5	–	5	–	
t_{OEE}	Output Enable Time from Output Enable	1	–	1	–	
t_{COD}	Output Disable Time from Chip Enable	–	6	–	8	
t_{ODO}	Output Disable Time from Output Enable	–	6	–	8	

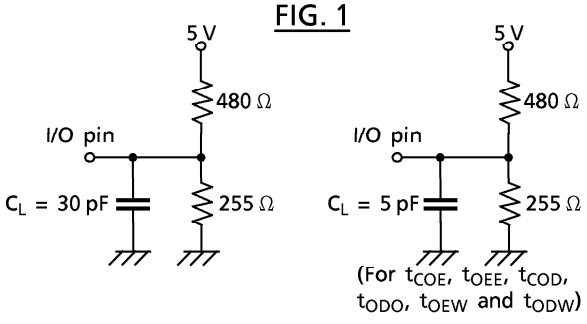
WRITE CYCLE

SYMBOL	PARAMETER	TC558128BJ/BFT-12		TC558128BJ/BFT-15		UNIT
		MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	12	–	15	–	ns
t_{WP}	Write Pulse Width	8	–	9	–	
t_{CW}	Chip Enable to End of Write	10	–	12	–	
t_{AW}	Address Valid to End of Write	10	–	12	–	
t_{AS}	Address Setup Time	0	–	0	–	
t_{WR}	Write Recovery Time	0	–	0	–	
t_{DS}	Data Setup Time	6	–	8	–	
t_{DH}	Data Hold Time	0	–	0	–	
t_{OEW}	Output Enable Time from Write Enable	1	–	1	–	
t_{ODW}	Output Disable Time from Write Enable	–	6	–	8	

AC TEST CONDITIONS

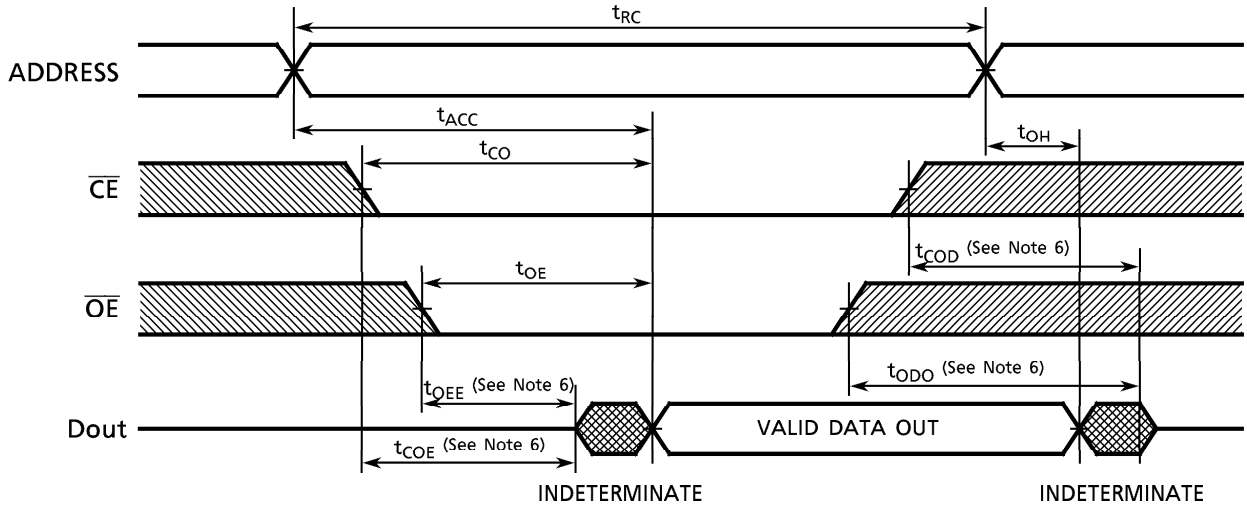
Input Pulse Level	3.0 V, 0.0 V
Input Pulse Rise and Fall Time	3 ns
Input timing Measurement Reference Level	1.5 V
Output Timing Measurement Reference Level	1.5 V
Output Load	Fig. 1

FIG. 1

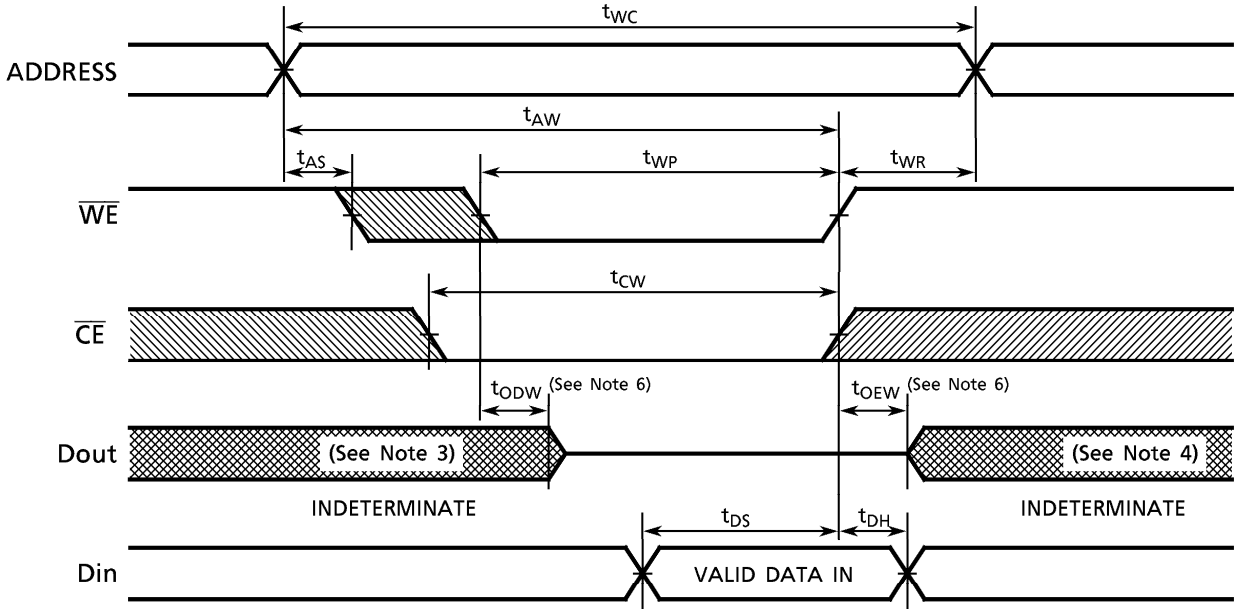


TIMING DIAGRAMS

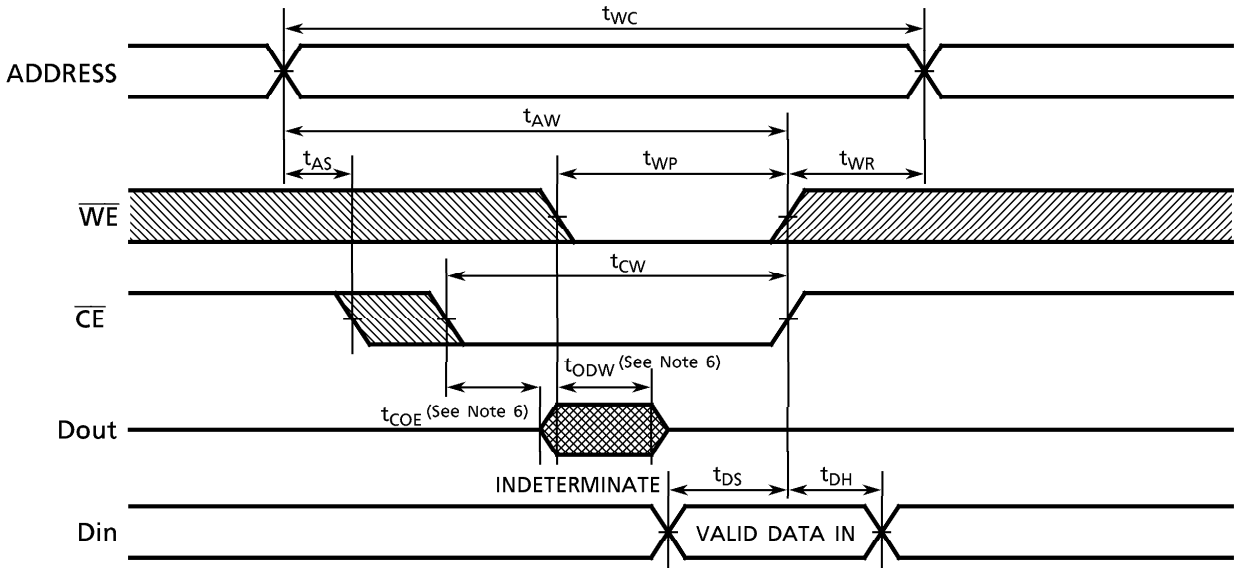
READ CYCLE (See Note 2)



WRITE CYCLE 1 ($\overline{WE}$ CONTROLLED) (See Note 5)



WRITE CYCLE 2 ($\overline{CE}$ CONTROLLED) (See Note 5)



Note: (1) Operating temperature (Ta) is guaranteed for transverse air flow exceeding 400 linear feet per minute.

(2) $\overline{WE}$ remains HIGH for the Read Cycle.

(3) If $\overline{CE}$ goes LOW coincident with or after $\overline{WE}$ goes LOW, the outputs will remain at high impedance.

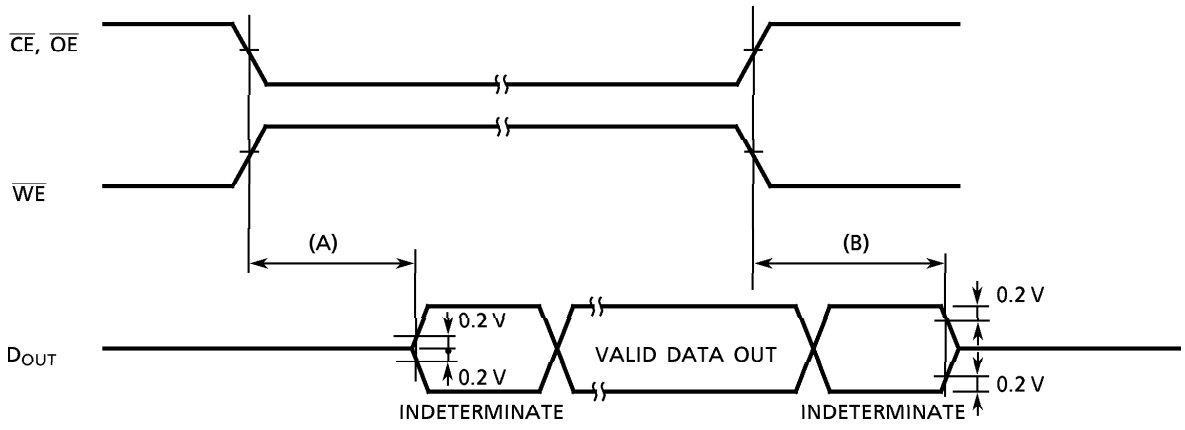
(4) If $\overline{CE}$ goes HIGH coincident with or before $\overline{WE}$ goes HIGH, the outputs will remain at high impedance.

(5) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

(6) The parameters specified below are measured using the load shown in Fig. 1.

(A) t_{COE}, t_{OEE}, t_{OEW} Output ····· Enable Time

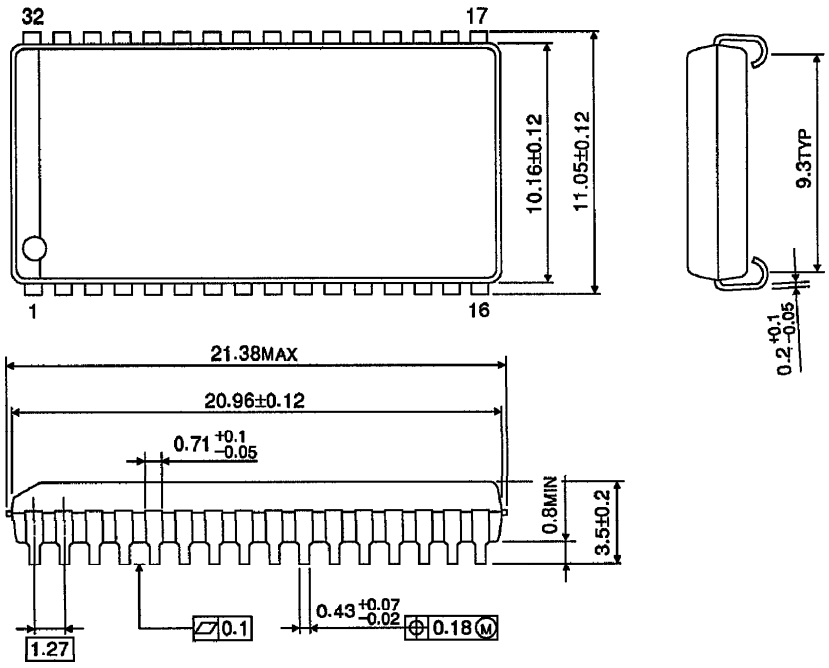
(B) t_{COD}, t_{ODO}, t_{ODW} Output ····· Disable Time



PACKAGE DIMENSIONS

Plastic SOJ (SOJ32-P-400-1.27A)

Units in mm

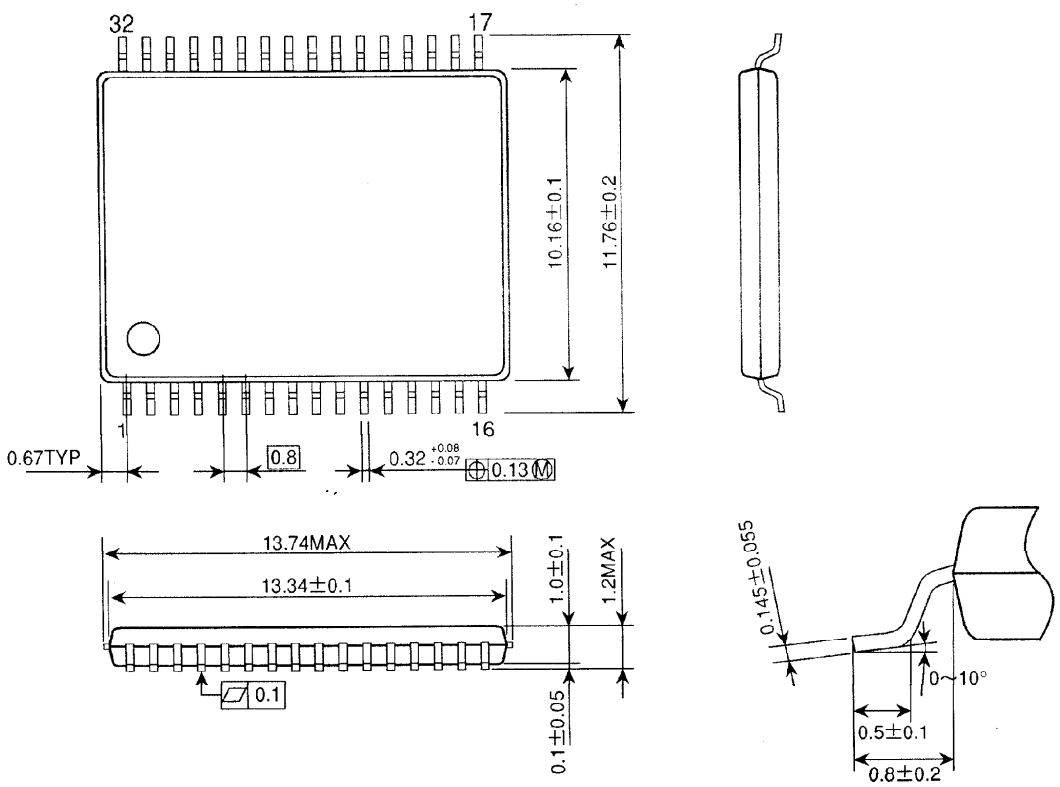


Weight: 1.22 g (typ)

PACKAGE DIMENSIONS

Plastic TSOP (TSOP II 32-P-400-0.80C)

Units in mm



Weight: 0.34 g (typ)